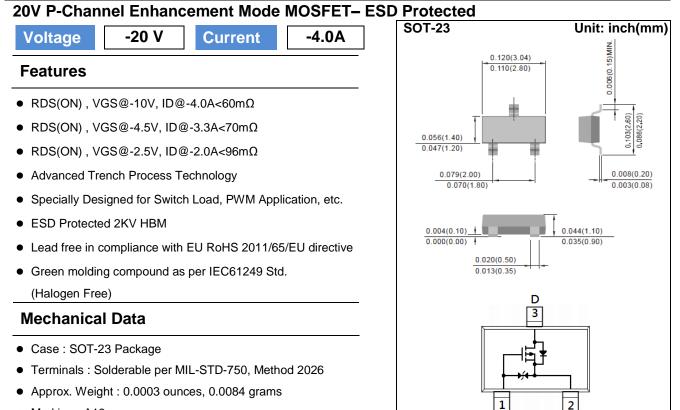
ΡΛΝ	JIT
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Marking : A19

#### **Maximum Ratings and Thermal Characteristics** ( $T_A=25^{\circ}C$ unless otherwise noted)

PARAMETE	PARAMETER		LIMIT	UNITS
Drain-Source Voltage		V <sub>DS</sub>	-20	V
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 12	V
Continuous Drain Current	ontinuous Drain Current		-4.0	А
Pulsed Drain Current (Note 4)		I <sub>DM</sub>	-16	А
Power Dissipation	T <sub>a</sub> =25°C	P <sub>D</sub>	1.25	W
	Derate above 25°C		10	mW/°C
Operating Junction and Storage Te	perating Junction and Storage Temperature Range		-55~150	°C
Typical Thermal resistance - Junction to Ambient <sup>(Note 3)</sup>		R <sub>θJA</sub>	100	°C/W



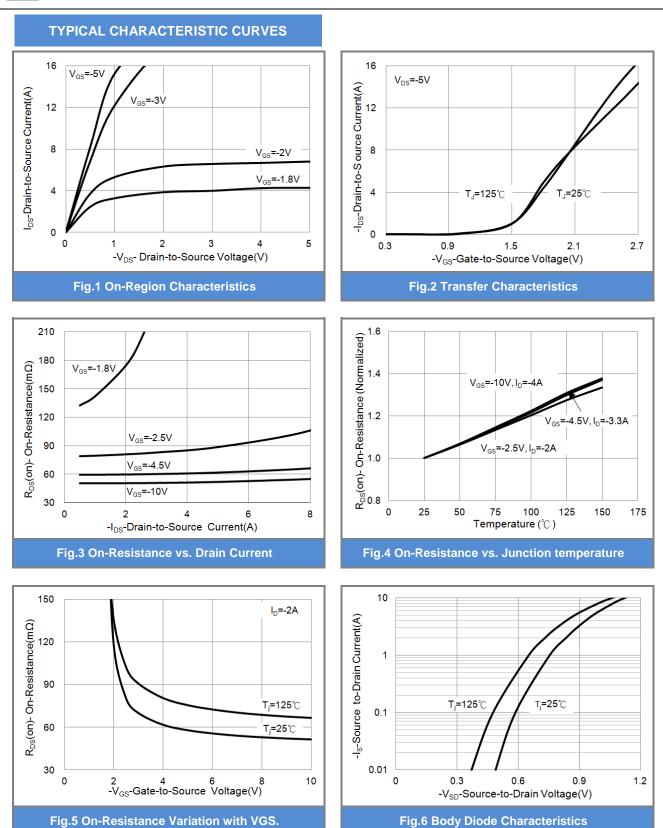
#### **Electrical Characteristics** ( $T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-20	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=-250$ uA	-0.5	-0.77	-1.2	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-4.0A	-	50	60	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3.3A	-	58	70	
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-2.0A	-	80	96	
		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-0.5A	-	140	180	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V	-	-	-1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 8V, V <sub>DS</sub> =0V	-	-	<u>+</u> 10	uA
Dynamic (Note 5)						
Total Gate Charge	Qg	V <sub>DS</sub> =-10V, I <sub>D</sub> =-4.0A, V <sub>GS</sub> =-4.5V <sup>(Note 1,2)</sup>	-	6.9	-	nC
Gate-Source Charge	$Q_gs$		-	1.5	-	
Gate-Drain Charge	$Q_gd$		-	1.9	-	
Input Capacitance	Ciss	$V_{DS}$ =-10V, $V_{GS}$ =0V,	-	602	-	
Output Capacitance	Coss		-	70	-	pF
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	47	-	
Turn-On Delay Time	td <sub>(on)</sub>		-	8.8	-	
Turn-On Rise Time	tr	$V_{DD}$ =-10V, $I_{D}$ =-4.0A, $V_{GS}$ =-4.5V, $R_{G}$ =3 $\Omega$ <sup>(Note 1,2)</sup>	-	66	I	ns
Turn-Off Delay Time	td <sub>(off)</sub>		-	29	I	
Turn-Off Fall Time	tf	$R_{G}=3\Omega$	-	14	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	I <sub>S</sub>		-	-	-1.5	А
Diode Forward Current	'3				1.0	
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =-1.0A, V <sub>GS</sub> =0V	-	-0.79	-1.0	V

NOTES :

- 1. Pulse width <300us, Duty cycle <2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. R<sub>0JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing







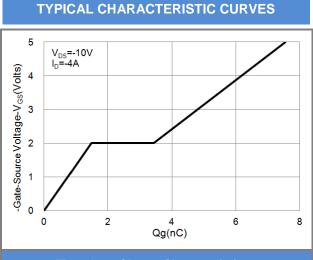


Fig.7 Gate-Charge Characteristics

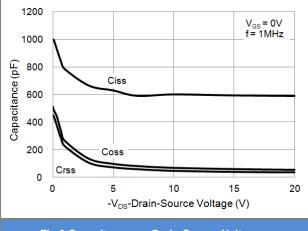
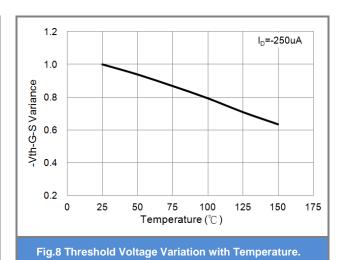


Fig.9 Capacitance vs. Drain-Source Voltage.



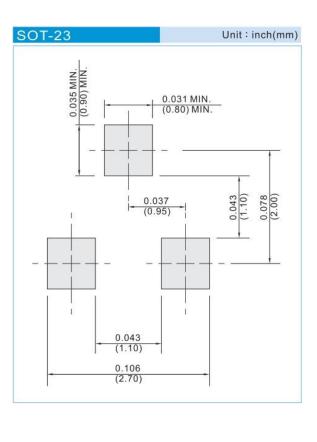




#### PART NO PACKING CODE VERSION

PART NO PACKING CODE	Package Type	Packing type	Marking	Version
PJA3419_R1_00001	SOT-23	3K pcs / 7" reel	A19	Halogen free
PJA3419_R2_00001	SOT-23	12K pcs / 13" reel	A19	Halogen free

#### **MOUNTING PAD LAYOUT**







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